## Notice of References Cited

Application/Control No. 10/197,651	Applicant(s)/Patent Under Reexamination GAJDA, MARK A.					
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Form PTO-1449 U.S. DEPARTMENT OF Atty. Docket No. Serial No. COMMERCE 10/197,651 (REV. 7-80) PATENT AND TRADEMARK OFFICE GB 010121 Applicant MARK A. GAJDA Filing Group 7/17/02 2812 **INFORMATION DISCLOSURE CITATION** (Use several sheets if necessary) **U.S. PATENT DOCUMENTS** Date Ex. Document Class Sub-Name Filing Date Int. Number class If Approp. AA AB AC AD ΑE **FOREIGN PATENT DOCUMENTS** Class Sub-Document Date Country Trans. Number class No Yes 11/1/96 GERMANY H01L 29/78 X AG 7/9/01 PCT (WORLD) H01L 29/78 0 0 1 6 5 6 0 8 x AН AI AJ AK OTHER (Including Author, Title, Date, Pertinent Pages, Etc.) Juang et al: "A process simplification scheme for fabricating self-aligned silicided trench-gate power MOSFETs" solid state Electronics, Elsevier Science Publishers, vol. WL 45, no. 1, January 2001, pages 169-172 Norstrom et al: "Formation of CoSi2 and TiSi2 on narrow poly-Si lines" Microelectronic WIL AM engineering, vol. 14, no. 3-4, September 1991, pages 327-339 AN

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Initial if reference considered, whether or not citation is in conformance with MPEP 609;

Draw line through citation if not in conformance and not considered. Include a copy of

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Examiner

EXAMINER:

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